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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s): Jack H. Yuan et al.  
Assignee: SanDisk Corporation  
Title: Scalable Self-Aligned Dual Floating Gate Memory Cell Array and Methods of Forming the Array  
Serial No.: 09/925,102 Filing Date: August 8, 2001  
Examiner: Unknown Group Art Unit: 2185  
Docket No.: M-11822 US Conf. No.: 3186

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PRELIMINARY AMENDMENT

Sir:

Please amend the above-identified patent application by adding the following new claims:

24. A non-volatile memory, comprising:  
an array of charge storage elements formed on a semiconductor substrate,  
field dielectric material positioned between the charge storage elements in at least one direction across the array, and  
electrically conductive control gates extending across tops of the array of charge storage elements in said at least one direction with a layer of dielectric positioned therebetween and protruding downward into slots formed in the field dielectric between adjacent ones of the charge storage elements, the downward portions of the control gates providing electrical shielding between adjacent charge storage elements in said one direction.

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LAW OFFICES OF  
SKJERVEN MORRILL LLP  
3 EMBARCADERO CENTER  
SUITE 2800  
SAN FRANCISCO, CA 94111  
(415) 217-6000  
FAX (415) 434-0646